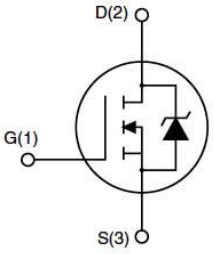
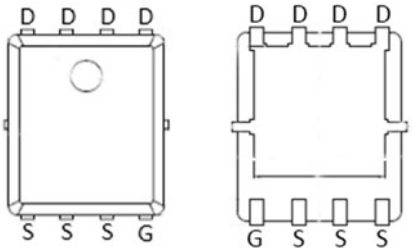
Feature

- 60V,95A
  $R_{DS(ON)}$ <2.5mΩ @V_{GS}=10V
  $R_{DS(ON)}$ <3.4mΩ @V_{GS}=4.5V
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Application

- PWM applications
- Load Switch
- Power management



PDFN5X6-8L

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G025N06G	APG025N06G	PDFN5*6-8L	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (T_a =25℃)	I_D	95	A
Continuous Drain Current (T_a =100℃)	I_D	60	A
Pulsed Drain Currenr (1)	I_{DM}	390	A
Singel Pulsed Avalanche Energy (2)	E_{AS}	500	mJ
Power Dissipation	P_D	120	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.04	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	60	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} =60V, V_{GS} = 0V	-	-	1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage(3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1.0	1.8	2.5	V
Drain-source on-resistance(3)	$R_{DS(on)}$	V_{GS} =10V, I_D =20A	-	2.1	2.5	mΩ
		V_{GS} =4.5V, I_D =15A	-	2.7	3.4	
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =25V, V_{GS} =0V, f =100KHz	-	5950	-	pF
Output Capacitance	C_{oss}		-	1250	-	
Reverse Transfer Capacitance	C_{rss}		-	85	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{DD}=30V, I_D=25A, R_L=2Ω V_{GS}=10V, R_G=3Ω	-	22.5	-	ns
Turn-on rise time	t_r		-	6.7	-	
Turn-off delay time	$t_{d(off)}$		-	80.3	-	
Turn-off fall time	t_f		-	26.9	-	
Total Gate Charge	Qg	VDS=50V, ID=50A, VGS=10V	-	93	-	nC
Gate-Source Charge	Qgs		-	17	-	
Gate-Drain Charge	Qgd		-	14	-	
Reverse Recovery Chrage	Qrr	I_F=25A,di/dt=100A/us		73		nC
Reverse Recovery Time	Trr	I_F=25A,di/dt=100A/us		68		ns
Source-Drain Diode characteristics						
Diode Forward voltage(3)	V_{DS}	V_{GS} =0V, I_S=30A	-	-	1.2	V
Diode Forward current(4)	I_S		-	-	95	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition:T_J=25℃,V_{DD}=50V,R_G=25Ω,L=0.5mH
3. Pulse Test: pulse width≤300μs, duty cycle≤2%
4. Surface Mounted on FR4 Board,t≤10 sec

■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

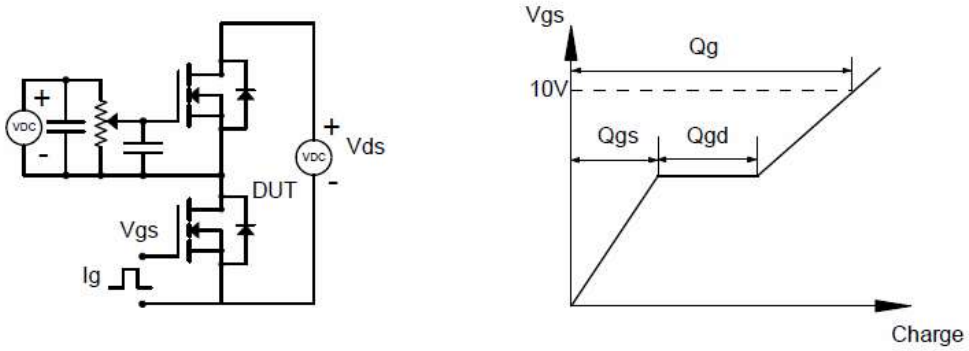


Figure B: Resistive Switching Test Circuit & Waveforms

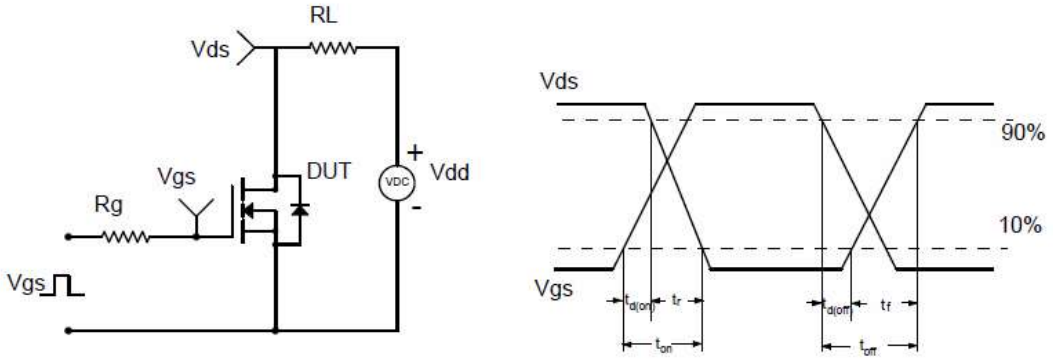


Figure C: Unclamped Inductive Switching (UIS) Test

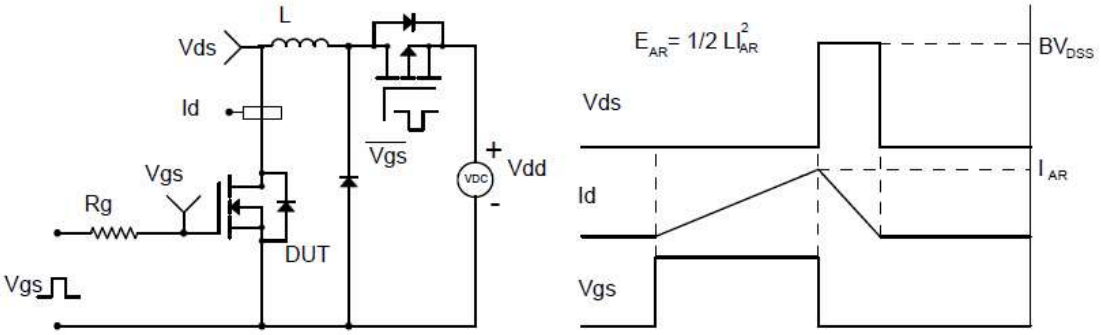
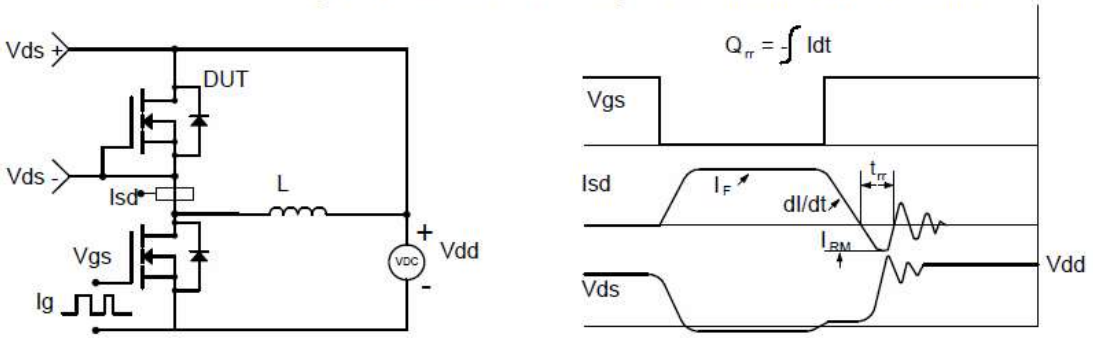


Figure D: Diode Recovery Test Circuit & Waveforms



■ Typical Performance Characteristics

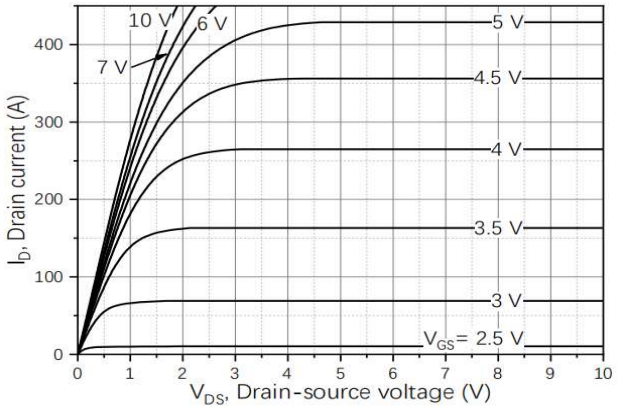


Figure1. Output Characteristics

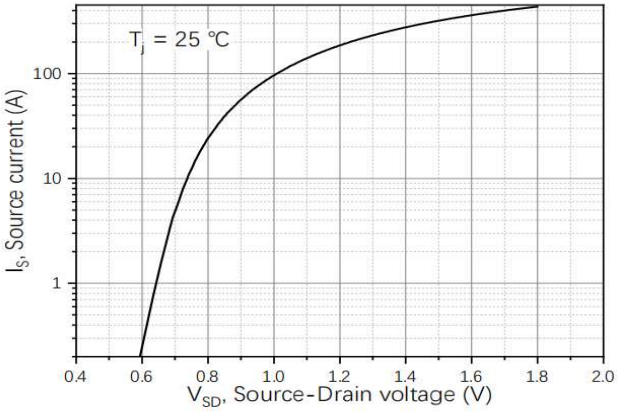


Figure2. Transfer Characteristics

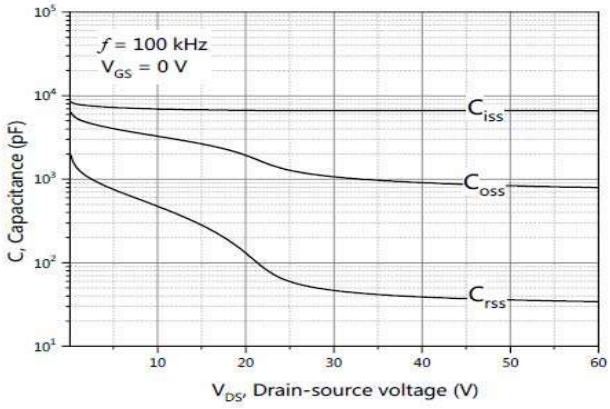


Figure3. Capacitance Characteristics

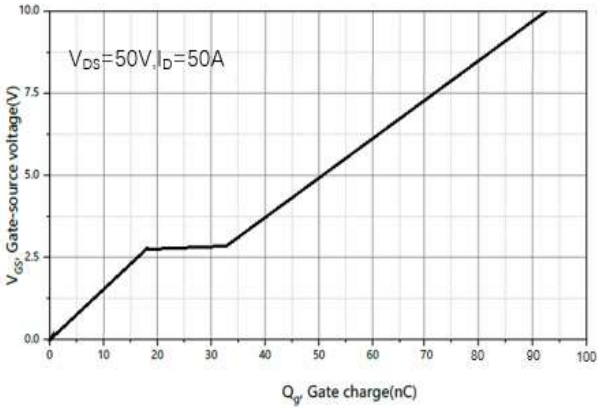


Figure4. Gate Charge

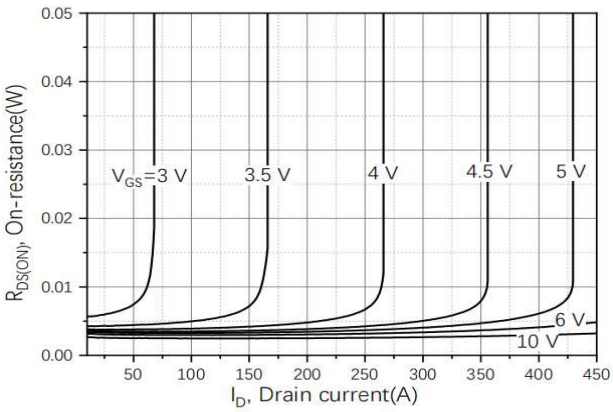


Figure5. Drain-Source on Resistance

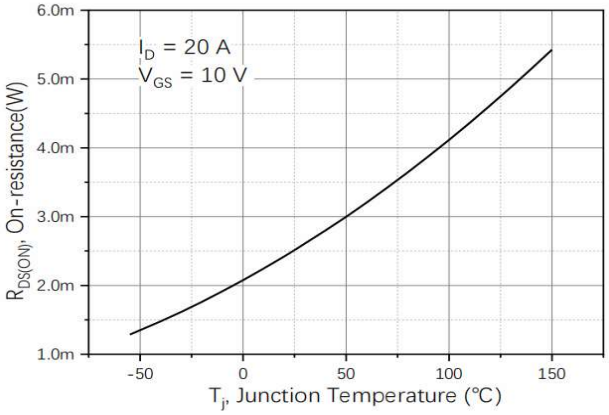


Figure6. Drain-Source on Resistance

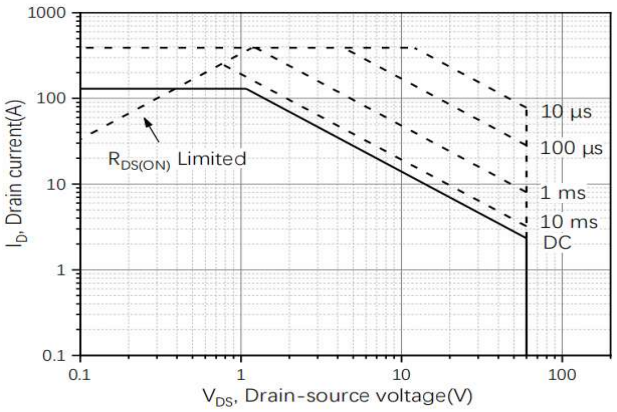


Figure7. Safe Operation Area

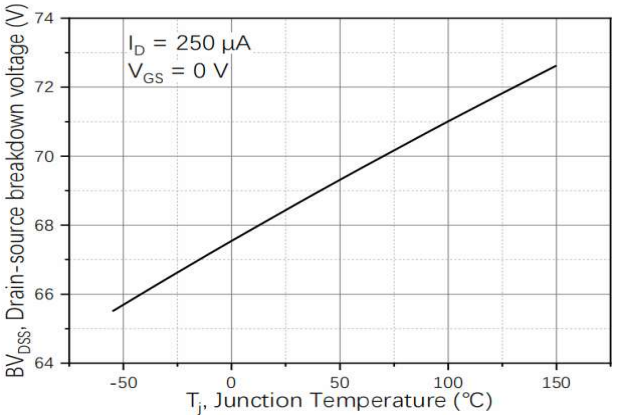


Figure8. Drain-source breakdown voltage

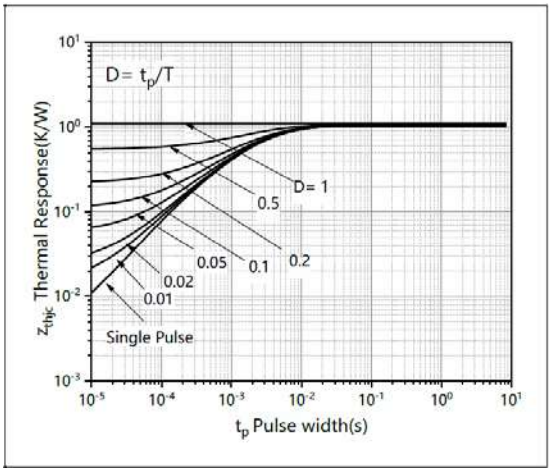
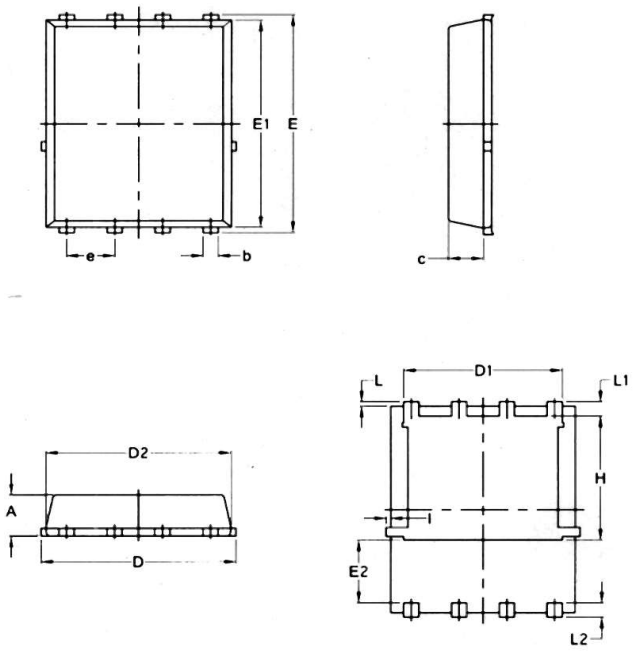


Figure 9.Transient thermal impedance

PDFN5*6-8L Package Information



PDFN5X6-8L

SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	—	0.0630	—
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	—	0.18	—	0.0070